


Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	31	flash same update same version same compar\$3	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 15:21
L2	29	update near3 parameter with flash	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 15:21
L1	49	update with flash with parameter	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 15:02
S71	38	flash with characteri\$6 with (select\$3 optim\$7) with \$2writ\$3	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 15:01
S68	593	flash with characteri\$6 with (select\$3 optim\$7)	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:54
S70	0	flash with characteri\$6 with (select\$3 optim\$7) with update	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:53
S69	4	flash with characteri\$6 with (select\$3 optim\$7) with lot	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:53
S67	6	flash with characterization with (select\$3 optim\$7)	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:52
S66	0	flash with characterization same updat\$3	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:48
S65	0	flash with characterization same update	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:48
S64	167	flash with characterization	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:48
S63	1	("5434094").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/26 13:48
S62	2	("6458611").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/26 13:47
S61	22	S58 and update	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:46

S60	0	S58 and S59	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:45
S59	2111	flash with update	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:45
S58	3787	(438/17).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/26 13:45
S57	17	flash with test with update	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:45
S56	16	flash with parameter with rewrit\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:39
S55	0	flash with parameter with rewrit\$3 with depend\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:31
S54	2	flash with voltage with rewrit\$3 with depend\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:31
S53	1	flash with voltage with rewrit\$3 with optim\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:30
S52	6	flash with voltage with rewrit\$3 with select\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:28
S51	1	flash with voltage with rewrit\$3 with update	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:25

S49	4	flash with voltage with rewrit\$3 with var\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:24
S48	267	flash with voltage with rewrit\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:24
S47	18221	flash with voltage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:21
S46	282558	flash withvoltage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:21
S45	27447	flash same voltage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:21
S44	3	flash same voltag	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:21
S43	21	characteristic with lot same flash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 13:21
S42	14	characteristic with lot same update	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 12:37
S41	2	characteristic with lot with test same update	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 12:37
S40	1	characteristic with lot with test same flash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 12:36

S39	151	characteristic with lot with test	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/26 12:36
S38	1	"6456554".pn.	DERWENT	OR	ON	2005/05/26 12:35
S37	2	"2000021694"	DERWENT	OR	ON	2005/05/26 12:35
S32	10	characteristic with lot with test	DERWENT	OR	ON	2005/05/26 12:35
S36	1	JP2000021694A	DERWENT	OR	ON	2005/05/26 12:32
S35	0	"Manufacture specification indication arrangement in semiconductor device - has information recording area formed on semiconductor chip, in which data relating to manufacture lot and serial number of wafer are recorded"	DERWENT	OR	ON	2005/05/26 12:32
S34	0	"02000021694"	DERWENT	OR	ON	2005/05/26 12:31
S33	0	"02000021694".oref.	DERWENT	OR	ON	2005/05/26 12:31
S1	0	2000-0040430	DERWENT	OR	ON	2005/05/26 12:22


[Web](#) [Images](#) [Groups](#) [News](#) [Froogle](#) [Local](#) [more »](#)

[Advanced Search](#)
[Preferences](#)

WebResults 1 - 10 of about 9,050 for **flash memory rewriting voltage**. (0.28 seconds)

[PDF] [Application Note-07 DATA PROTECTION METHOD OF W28XXX SERIES FLASH](#)

File Format: PDF/Adobe Acrobat

... To protect any data against inadvertent **rewriting** under such situation, ... supply **voltage**, the **flash memory** is disabled and the erasing/writing in all ...
www.winbond-usa.com/products/whitep/APNMNV07.pdf - [Similar pages](#)

Sponsored Links

[Flash Memory Store .com](#)Large selection of **Flash Memory!**

Save Money - Prices Start at \$9

[Flash-Memory-Store.com](#)

[PDF] [Application Note-08 #RESET, V ELECTRIC POTENTIAL SWITCHING CIRCUIT ...](#)

File Format: PDF/Adobe Acrobat

... on the power supply or resetting by the #RESET pin, the **flash memory** usually enters a ... **rewriting** due to the command mis-recognition can be prevented. ...
www.winbond-usa.com/products/whitep/APNMNV08.pdf - [Similar pages](#)

[SANYO Flash microcontrollers - Technical Advantages](#)

... Sanyo microcontrollers that incorporate **Flash EEPROM** feature simple control circuits, single-**voltage** power ... Types of **flash memory** and their features ...

www.semic.sanyo.co.jp/micon/eng/flash/total_contents.htm - 7k - [Cached](#) - [Similar pages](#)
[FAQ : FUJITSU](#)Frequently-asked question about **flash memory** for F2MC-16LX Family microcontroller. ...The Fujitsu's **Flash** microcomputer can perform **rewriting** sufficiently ...
www.fujitsu.com/global/services/microelectronics/product/micom/support/faq/16lx/flash.html - 39k - [Cached](#) - [Similar pages](#)
[FRAM Guide Book : FUJITSU](#)... enable low-**voltage** read and write operations, making this an ideal **memory** for ...**Rewriting** data on **Flash Memory** requires that data must be erased by ...
www.fujitsu.com/global/services/microelectronics/technical/fram/index_2.html - 37k - [Cached](#) - [Similar pages](#)
[64-Mbit AND-Type Flash Memory](#)

... this **flash memory** device allows the high **voltage** required for **rewriting** to be generated on the chip, so the chip can run on a single 3.3-V power supply. ...

www.hitachi.com/New/cnews/E/1996/960208B.html - 9k - [Cached](#) - [Similar pages](#)
[PDF] [Hitachi Announced "superAND Type Flash Memory".](#)

File Format: PDF/Adobe Acrobat

... wear leveling function can increase the life span of **rewriting** of **flash memory**. ...**Memory**. Structure. Operation. **Voltage**. Package. Price for 100000 ...
www.hitachi.com/New/cnews/E/2002/0402/0402.pdf - [Similar pages](#)
[2.FLASH IP Design Techniques](#)... it is necessary to make the threshold **voltage** of the **memory** cells greater ... With this**FLASH IP** an interface circuit for **rewriting** the following three ...
www.oki.com/en/otr/html/nf/otr-184-09-2.html - 8k - [Cached](#) - [Similar pages](#)
[Jairamdas Group - News Flash](#)

... function can increase the life span of **rewriting** of **flash memory**. ... The product of operation **voltage** 1.8 V and x 16 bits is also equipped with a ...

www.jairamdas.com/n9.htm - 18k - [Cached](#) - [Similar pages](#)